Revision 1.11



2019-03-01

# **GAIN CHIPS AR coated Fabry-Perot Laser**



Genera	Product	Information
--------	---------	-------------

Product	Application
tunable 840 nm Fabry-Perot Laser	Spectroscopy
for use in an External Cavity Diode Laser (ECDL)	Covering popular wavelengths
sealed SOT Housing	between 810 and 860 nm
Monitor Diode	



## Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	$T_S$	°C	-40		85
Operational Temperature at Case	$T_{C}$	°C	-20		50
Forward Current	I <sub>F</sub>	mA			200
Reverse Voltage	$V_R$	V			0
Output Power (extracavity)	$P_{\text{opt}}$	mW			100

### **Measurement Conditions / Comments**

Stess in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

## Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T <sub>C</sub>	°C	15		40
Forward Current	I <sub>F</sub>	mA			180

Measurement Conditions / Comments

# Characteristics at T<sub>LD</sub>= 25 °C at BOL, with external cavity under recommended working condition

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	$\lambda_{C}$	nm		840	
Tuning Range	$\Delta \lambda_{tun}$	nm	810		860
Output Power	$P_{\text{opt}}$	mW		50	
Polarization				TE	
Output Power	$P_{\text{opt}}$	W		50	
Spatial Mode (transversal)				TEM00	

### Measurement Conditions / Comments

The actual achieved wavelength and power are strongly influenced by the external cavity. eyP gives no guarantee on these parameters.

E field parallel to Pin 2 - Pin 3 - plane

Fundamental Mode



Revision 1.11

# **GAIN CHIPS AR coated Fabry-Perot Laser**



# Amplified Spontaneous Emission (ASE) without external cavity

Parameter	Symbol	Unit mir	n typ	max
Divergence parallel (FWHM)	$\Theta_{  }$		10	
Divergence perpendicular (FWHM)	$\Theta_{\perp}$		23	
Monitor Detector Responsivity	I <sub>mon</sub> / P <sub>ASE</sub> μΑ	A/mW 1		40

Measurement Conditions / Comments
parallel to Pin 2 - Pin 3 plane (see p. 3)
perpendicular to Pin 2 - Pin 3 plane (see p. 3)
$U_{R MD} = 5 V$

#### 

Measurement Conditions / Comments				

Revision 1.11



# **GAIN CHIPS AR coated Fabry-Perot Laser**



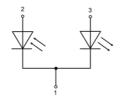
## Package Dimensions

Parameter	Symbol	Unit	min	typ	max
Height of Emission Plane	h	mm	3.50	3.65	3.70
Excentricity of Emission Center	R	mm			0.12
Pin Length	$L_{PIN}$	mm		14	

Measurement Conditions / Comments
reference plane: top side of TO header
reference: center of outer diameter of header

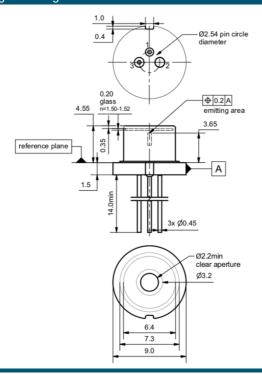
## Package Pinout

- 1 Laser Diode Cathode, Monitor Diode Cathode, Case
- 2 Photo Diode Anode
- 3 Laser Diode Anode





## Package Drawings





AIZ-16-0421-1517

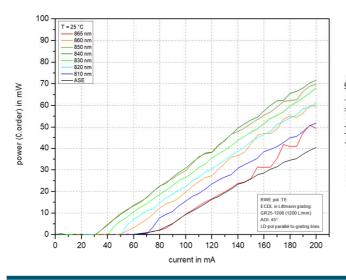
Revision 1.11

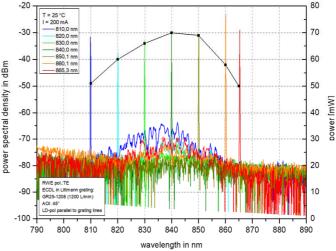


# **GAIN CHIPS AR coated Fabry-Perot Laser**



## Typical Measurement Results





### Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The TPA diode type is known to be sensitive against thermal stress. It should not be operated without appropriate injection from a seed laser. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode. The chip should be protected against moisture. A water vapor content below 5000 ppm is recommended for applications with high reliability requirements.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.







INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE
TO DIRECT OR SCATTERED RADIATION
CLASS 4 LASER PRODUCT
WAVELENGTH 840 nm
MAX. OUTPUT POWER 100 mW







